The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A light emitting device comprising:

a pixel portion having an n-channel TFT and a light emitting element over a substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer; and

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film;

a protecting film in contact with the gate insulating layer and the second conductive film,

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film.

2. (Currently Amended) A light emitting device comprising:

a driver circuit having an n-channel TFT over a substrate; and

a pixel portion having a light emitting element over the substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer; and

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film;

a protecting film in contact with the gate insulating layer and the second conductive film,

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film.

3. (Previously Presented) The light emitting device as claimed in claim 1, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

4. (Previously Presented) The light emitting device as claimed in claim 2, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

5. (Previously Presented) The light emitting device as claimed in claim 1, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

6. (Previously Presented) The light emitting device as claimed in claim 2, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

7. (Previously Presented) The light emitting device as claimed in claim 1, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

8. (Previously Presented) The light emitting device as claimed in claim 2, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

9. (Previously Presented) The light emitting device as claimed in claim 1, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

10. (Previously Presented) The light emitting device as claimed in claim 2, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

11. (Previously Presented) The light emitting device as claimed in claim 9, wherein a coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

12. (Previously Presented) The light emitting device as claimed in claim 10, wherein a coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

13. (Previously Presented) The light emitting device as claimed in claim 1, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

14. (Previously Presented) The light emitting device as claimed in claim 2, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

15.-24. (Canceled)

25. (Currently Amended) A light emitting device comprising:

a pixel portion having an n-channel TFT and a light emitting element over a substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer;

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film,

a coloring layer over the gate electrode:

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film.

26. (Currently Amended) A light emitting device comprising:

a driver circuit having an n-channel TFT over a substrate; and

a pixel portion having a light emitting element over the substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer;

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film,

a coloring layer over the gate electrode:

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and the second conductive film has a thinner width as compared with the first conductive film.

27. (Previously Presented) The light emitting device as claimed in claim 25, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

28. (Previously Presented) The light emitting device as claimed in claim 26, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

29. (Previously Presented) The light emitting device as claimed in claim 25, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

30. (Previously Presented) The light emitting device as claimed in claim 26, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

31. (Previously Presented) The light emitting device as claimed in claim 25, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

32. (Previously Presented) The light emitting device as claimed in claim 26, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

33. (Previously Presented) The light emitting device as claimed in claim 25, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

34. (Previously Presented) The light emitting device as claimed in claim 26, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

35. (Previously Presented) The light emitting device as claimed in claim 33, wherein the coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

36. (Previously Presented) The light emitting device as claimed in claim 34, wherein the coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

37. (Previously Presented) The light emitting device as claimed in claim 25, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

38. (Previously Presented) The light emitting device as claimed in claim 26, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

39.-50. (Canceled)

51. (Previously Presented) A light emitting device comprising:

a pixel portion having an n-channel TFT and a light emitting element over a substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer; and

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film,

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween,

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and

wherein the gate insulating layer has a greater thickness over the channel forming region than over the n-type impurity region (a).

52. (Previously Presented) A light emitting device comprising:

a driver circuit having an n-channel TFT over a substrate; and

a pixel portion having a light emitting element over the substrate,

wherein the n-channel TFT comprises:

an active layer including:

a channel forming region;

an n-type impurity region (c) adjacent to the channel forming region;

an n-type impurity region (b) adjacent to the n-type impurity region (c); and

an n-type impurity region (a) adjacent to the n-type impurity region (b);

a gate insulating layer provided over the active layer; and

a gate electrode provided over the gate insulating layer, the gate electrode including:

a first conductive film provided over the gate insulating layer; and

a second conductive film provided over the first conductive film,

wherein the first conductive film overlaps the channel forming region and the n-type impurity region (c) with the gate insulating layer interposed therebetween, and

wherein the second conductive film overlaps the channel forming region with the gate insulating layer and the first conductive film interposed therebetween, and

wherein the gate insulating layer has a greater thickness over the channel forming region than over the n-type impurity region (a).

53. (Previously Presented) The light emitting device as claimed in claim 51, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

54. (Previously Presented) The light emitting device as claimed in claim 52, wherein the first conductive film comprises one of tantalum nitride and titanium nitride, and the second conductive film comprises tungsten.

55. (Previously Presented) The light emitting device as claimed in claim 51, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

56. (Previously Presented) The light emitting device as claimed in claim 52, wherein the first conductive film comprises tungsten, and the second conductive film comprises aluminum.

57. (Previously Presented) The light emitting device as claimed in claim 51, wherein the n-type impurity region (a) includes an n-type impurity element in concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

58. (Previously Presented) The light emitting device as claimed in claim 52, wherein the n-type impurity region (a) includes an n-type impurity element in

concentrations from $1x10^{20}$ to $1x10^{21}$ atoms/cm^3, the n-type impurity region (b) includes an n-type impurity element in concentrations of from $2x10^{16}$ to $5x10^{19}$ atoms/cm^3, and the n-type impurity region (c) includes an n-type impurity element in concentrations from $1x10^{16}$ to $5x10^{18}$ atoms/cm^3.

59. (Previously Presented) The light emitting device as claimed in claim 51, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

60. (Previously Presented) The light emitting device as claimed in claim 52, wherein the gate electrode is covered by an insulating film comprising at least one of a silicon nitride film and a silicon oxynitride film.

61. (Previously Presented) The light emitting device as claimed in claim 59, wherein a coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

62. (Previously Presented) The light emitting device as claimed in claim 60, wherein a coloring layer is provided between a resin film and the silicon nitride film or between the resin film and the silicon oxynitride film.

63. (Previously Presented) The light emitting device as claimed in claim 51, wherein the light emitting device is one selected from the group consisting of an EL display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.

64. (Previously Presented) The light emitting device as claimed in claim 52, wherein the light emitting device is one selected from the group consisting of an EL

display, a video camera, a digital camera, a portable computer, a personal computer, a portable telephone, and a car audio stereo.